

LED CHIP C630-55V

SPECIFICATION OF LED CHIP  
C630-55V  
[RED]

1) Commodity Type and Physical Characteristics.

- 1. Material InGaAlP/GaAs
- 2. Electrode Top Side P (anode) side :Au Alloy/Al or Au Pad  
Bottom Side N (cathode) side :Au Alloy
- 3. Electrode Pattern Fig.1
- 4. Chip Size Fig.2
- 5. Chip Thickness Fig.2
- 6. Emission Area Fig.2

2) Electro-Optical Characteristics [Ta=25°C]

Parameters	Symbol	Condition	Min.	Type	Max.	Unit
Forward Voltage	Vf	If=20mA		1.90	2.30	V
Forward Voltage	Vf	If=500mA		3.00	4.50	V
Reverse Current	Ir	Vr=5V			10	uA
Brightness	Iv	If=20mA	70	120		mcd
Power Intensity	Po	If=20mA	0.7	1.2		mW
Peak Wavelength	λp	If=20mA	625	635	645	nm
Spectral Bandwidth	Δλ	If=20mA		15		nm
Rise Time	tr	If=20mA		100		ns
Fall Time	tf	If=20mA		100		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.

[Unit: um]

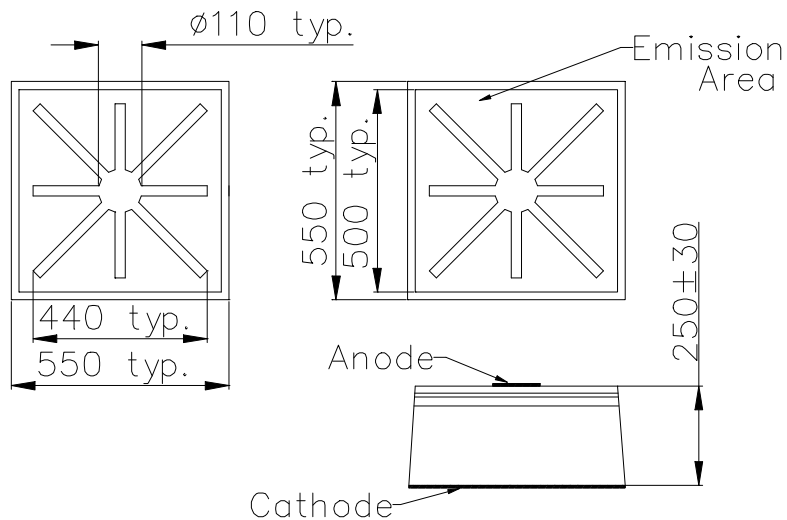


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area